The Semiconductor Drift Detector (SDD)

The Concept of Semiconductor Drift Detector History of the development

Transport of charged carriers in thin fully depleted semiconductor detectors in direction parallel to the large surface of the detector.



0.3 mm

Reverse-biased one sided step p-n junction in 1dimension



Depletion from two sides



SDD principle



Low capacitance anode



The first signals from a SDD



BUC, 1983

The classical PIN diode detector



The anode capacitance is proportional to the detector active area

The SDD for X-ray spectroscopy



Anode

The electrons are collected by the small anode, characterised by a **low output capacitance** which is **independent on the active area of the detector**.

The SDD structure



The electrons, generated in the fully depleted silicon by the X-ray photons, are collected by the small anode (having a very low capacitance, Cdet=150fF). The integrated front-end transistor (n-JFET) allows the capacitive matching between detector and amplifier(Cdet≈Cgate)

Advantages: very high energy resolution at fast shaping times, due to the small anode capacitance, independent of the active area of the detector

The integrated JFET



Detector produced at the MPI Halbleiterlabor, Munich, Germany

SDD performances



 ⁵⁵Fe spectrum measured with the SDD module at T= -8°C and a shaping time of 0.5 μs.

The integrated JFET



The "conventional" central anode containing the FET



The "lateral" anode with side FET



The new Silicon Drift Detector Droplet (SD³)





The resolution of the new SD³



Performances with soft X-ray



Some applications of the single-element SDDs in X-ray spectroscopy

Analysis of the alloy composition of the 'Lupa Capitolina'



Musei Capitolini, Roma

XRF spectrum of the bronze alloy of the 'Lupa'



Element distribution on the 'Lupa' body





Analysis of the alloy composition of the "Spinario"



Musei Capitolini, Roma

Analysis of a bronze roman sculpture





Correlation diagrams of the bronze composition of several points of the head and of the body of the sculpture, showing that the two parts have been produced with different fusion (maybe in a different historical period). The last diagram shows that Ni has been probably introduced as impurity of Sn.

Analysis of an Egyptian Linen (Antinopolis, III century A.C.)



Museo Vaticano, Roma



Authenticity verification



Fluorescence spectra of a document in a reference point (a) and in a point where stain remover was supposed to be applied (b) (the spectra are normalized with respect to the Ti-K_{α} line). In (c) the difference between the two spectra (a) and (b) is reported, revealing a probable application of a conventional stain remover containing S, K, and Mn.

Multi-element SDDs

The 12-element SDD detector



The 12-element SDD detector



Detector performances



⁵⁵Fe radioactive source – T = -10 °C – Tennelec TC244 gaussian shaping amplifier $\tau_{sh} = 0.5 \ \mu s$ Count rate $\approx 10 \ \text{kcps}$ / channel. Average FWHM: 154.7 eV

A new multi-element Semiconductor Srift Detector optimized for XRF Elemental Mapping



Project FELIX INFN Gr.5 2003-04

A new multi-element Semiconductor Srift Detector optimized for XRF Elemental Mapping



Thickness 450 µm



Front side Collecting anode and transistor

Back side Radiation entrance window

SDD4 collimator



Collimated area $\approx 4 \text{ x } 15 \text{ mm}^2$

SDD4: collecting region


SDD4 potential energy



SDD4 preliminary results



SDD4 preliminary results

Peak to valley ratio



Tsh=500ns Beam collimated: Ø≈500µm

SDD4 preliminary results Resolution vs count rate



SDD4 measurement head setup



The ceramic board with electronic components



The collimator





The Peltier refrigerators and the Be windows





Readout electronics + Data acquisition system for the SDD4



Scheme of principle of the new fast acquisition system presently under development (the histogram is made 'on board')

Researchers involved: A.Longoni, C.Guazzoni, S.Buzzetti

PRESTAZIONI DEL NUOVO SISTEMA DI ACQUISIZIONE



Rate performance

Some applications of the multi-element SDDs

The concept of the multi-element spectrometer for XRF elemental mapping



Researchers involved: A.Longoni, C.Fiorini

A polycapillary X-ray lens allows:

an higher photon flux in a small excitation spot







A multi-element detector allows:

•an higher detection rate for the same total active area

The excitation-detection unit

Microfocus X-ray generator * W anode 50 kV max DC voltage, 30 W max anode load



The X-ray mini-lens parameters







Measured with 15 µm pinhole



Geology



Chromite



Chromite: main elements







Lombard buckle – inlaid work (agemina) Second quarter of VII century A.C. Trezzo d'Adda, Italy













Mretallurgy: study of an Iron-Nichel alloy

Fe





Iron powder with Nickel grains partially diffused on the Iron surface during the syntherization process at 1120 C



Leaf 'fluorescence' (detail)



Scanned area 6x6 mm, 61x61 points, 100µm x 100µm pitch, 0.5s meas time per point, 6 SDD active Max counts/pixel: K 406 Ca 2386 Mn 1902 Fe 3822 Cu 6874

Leaf 'radiography' (detail)



Absorption of K α Ca line (3.69 keV) Scan: 21x21points, 250 μ m x 250 μ m steps, measurement time 1s/point

Technology





The Gamma ray imaging detectors

SDD arrays coupled with a scintillator crystal

Development of a small Anger Camera for high position resolution γ-ray imaging

Applications in Medical Imaging:





- compact diagnostic systems for human imaging (thyroid gland diagnostic, brain imaging, breast imaging..)
- small animal imaging systems with < 0.5 mm position resolution

The first prototype of SDD - CsI(TI) Anger camera



Total area = $5 \text{ mm}^2 \times 19 \sim 1 \text{ cm}^2$

CsI(TI) thickness = 3 mmT = -10° C

E = 122 keV (57 Co)



C.Fiorini, et al., Nucl. Instr. Meth., Vol. A512, 2003.

SDD - CsI(TI) Anger camera: final results




γ-ray Imaging







The monolithic array of 77 SDDs: front side



- 77 units, 8.7 mm² each
- \Rightarrow active area = 6.7 cm²
- active area: $29 \times 26 \text{ mm}^2$
- two interconnection layers available (polysilicon, Al)

 output pads for bias/signals placed outside the active area

Detector back side



Preliminary caracterization of the whole array: ⁵⁵Fe spectra measured with bias optimized for each unit



room T

$$\begin{split} \tau_{shaping} &= 0.25 \mu s \\ V_{BACK} \text{ optimized for} \\ each unit: -76V \div -94V \\ (alternatively R#1 can \\ be optimized for each \\ unit, with the same results) \end{split}$$

noise is good and uniform among all units

(3 units are not working)

The DRAGO project *

(DRift detector Array-based Gamma camera for Oncology)



* Project INFN Gr.5 2003-05

The large-area SDDs

SDD 1cm² x 3 for the experiment SIDDHARTA INFN – EU 6° program



Radiation entrance window





Detector Setup



Conclusions

The Dectors here presented are today the best results of the "nearly old" idea of the the SDDs (E. Gatti and P. Rehak, 1983).

SDDs (under different commercial names) are nowadays widely used in several applications (SEMs, Synchrotrons, Portable XRF spectrometers, Mars exploration, ...).

Other devices derived from the original idea of Gatti and Rehak, the "fully depleted" PN-CCDs, are flying in a satellite for X-ray astronomy (XMM mission).

New devices, similarly derived from the original idea, are on the way: CDDs, DEPMOS pixel arrays, avalanche SDDs,

The INFN has believed in SDDs and has supported their development, in cooperation with the MPI Halblaiterlabor, from the very beginning of these devices.